

**Abstract of the Disclosure**

In one embodiment, the invention includes a field effect transistor having a substrate, a source, and a drain. An electric field terminal region is lower than the source and drain and is in the substrate. A body is above the electric field terminal region between the source and drain. In  
5 another embodiment, the invention includes a field effect transistor having an insulator layer and a body above the insulator layer between a source and a drain. A substrate is below the insulator layer. A gate is above the body and between the source and drain. An electric field terminal region is included in the substrate. The body may be undoped and the threshold voltage be set by setting the distance between the insulator layer and a gate insulator. The body, substrate, and  
10 electric field terminal region may float or one or more of them may be biased.

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